

# Jean Christophe Harmand

## List of Publications by Citations

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183  
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44  
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73  
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192  
ext. papers

6,697  
ext. citations

3.8  
avg, IF

5.54  
L-index

#	Paper	IF	Citations
183	Why does wurtzite form in nanowires of III-V zinc blende semiconductors?. <i>Physical Review Letters</i> , <b>2007</b> , 99, 146101	7.4	615
182	Growth kinetics and crystal structure of semiconductor nanowires. <i>Physical Review B</i> , <b>2008</b> , 78,	3.3	263
181	Analysis of vapor-liquid-solid mechanism in Au-assisted GaAs nanowire growth. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 203101	3.4	231
180	Crystal phase quantum dots. <i>Nano Letters</i> , <b>2010</b> , 10, 1198-201	11.5	207
179	Theoretical analysis of the vapor-liquid-solid mechanism of nanowire growth during molecular beam epitaxy. <i>Physical Review E</i> , <b>2006</b> , 73, 021603	2.4	154
178	Predictive modeling of self-catalyzed III-V nanowire growth. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	142
177	New mode of vapor-liquid-solid nanowire growth. <i>Nano Letters</i> , <b>2011</b> , 11, 1247-53	11.5	125
176	Au-assisted molecular beam epitaxy of InAs nanowires: Growth and theoretical analysis. <i>Journal of Applied Physics</i> , <b>2007</b> , 102, 094313	2.5	123
175	Arsenic Pathways in Self-Catalyzed Growth of GaAs Nanowires. <i>Crystal Growth and Design</i> , <b>2013</b> , 13, 91-96	11.5	119
174	Critical diameters and temperature domains for MBE growth of III-V nanowires on lattice mismatched substrates. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2009</b> , 3, 112-114	2.5	108
173	Growth of GaN free-standing nanowires by plasma-assisted molecular beam epitaxy: structural and optical characterization. <i>Nanotechnology</i> , <b>2007</b> , 18, 385306	3.4	103
172	Growth and characterization of InP nanowires with InAsP insertions. <i>Nano Letters</i> , <b>2007</b> , 7, 1500-4	11.5	102
171	Temperature conditions for GaAs nanowire formation by Au-assisted molecular beam epitaxy. <i>Nanotechnology</i> , <b>2006</b> , 17, 4025-30	3.4	101
170	Temperature-dependent valence band offset and band-gap energies of pseudomorphic GaAsSb on GaAs. <i>Journal of Applied Physics</i> , <b>2001</b> , 89, 5473-5477	2.5	96
169	Nucleation antibunching in catalyst-assisted nanowire growth. <i>Physical Review Letters</i> , <b>2010</b> , 104, 135504	7.4	95
168	Epitaxy of GaN Nanowires on Graphene. <i>Nano Letters</i> , <b>2016</b> , 16, 4895-902	11.5	94
167	Comparison of nitrogen incorporation in molecular-beam epitaxy of GaAsN, GaInAsN, and GaAsSbN. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 2482-2484	3.4	92

166	Role of nonlinear effects in nanowire growth and crystal phase. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	83
165	Atomic Step Flow on a Nanofacet. <i>Physical Review Letters</i> , <b>2018</b> , 121, 166101	7.4	82
164	GaNAsSb: how does it compare with other dilute IIIV-nitride alloys?. <i>Semiconductor Science and Technology</i> , <b>2002</b> , 17, 778-784	1.8	80
163	GaAsSbN: a new low-bandgap material for GaAs substrates. <i>Electronics Letters</i> , <b>1999</b> , 35, 1246	1.1	79
162	Growth kinetics of a single InP $_{1-x}$ As $_x$ nanowire. <i>Physical Review B</i> , <b>2010</b> , 81,	3.3	78
161	Room-temperature defect-engineered spin filter based on a non-magnetic semiconductor. <i>Nature Materials</i> , <b>2009</b> , 8, 198-202	27	78
160	Facet and in-plane crystallographic orientations of GaN nanowires grown on Si(111). <i>Nanotechnology</i> , <b>2008</b> , 19, 155704	3.4	77
159	Record pure zincblende phase in GaAs nanowires down to 5 nm in radius. <i>Nano Letters</i> , <b>2014</b> , 14, 3938-44	1.5	72
158	GaInAs/GaAs quantum-well growth assisted by Sb surfactant: Toward 1.3 $\mu$ m emission. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 3981-3983	3.4	70
157	Wide InP nanowires with wurtzite/zincblende superlattice segments are type-II whereas narrower nanowires become type-I: an atomistic pseudopotential calculation. <i>Nano Letters</i> , <b>2010</b> , 10, 4055-60	11.5	68
156	High-quality In $_x$ Ga $_{1-x}$ As/InAlAs modulation-doped heterostructures grown lattice-mismatched on GaAs substrates. <i>Journal of Crystal Growth</i> , <b>1991</b> , 111, 313-317	1.6	63
155	Wurtzite to zinc blende phase transition in GaAs nanowires induced by epitaxial burying. <i>Nano Letters</i> , <b>2008</b> , 8, 1638-43	11.5	60
154	Silicon nanowires: Diameter dependence of growth rate and delay in growth. <i>Applied Physics Letters</i> , <b>2010</b> , 96, 133109	3.4	58
153	Morphology of self-catalyzed GaN nanowires and chronology of their formation by molecular beam epitaxy. <i>Nanotechnology</i> , <b>2011</b> , 22, 245606	3.4	55
152	Diffusion-controlled growth of semiconductor nanowires: Vapor pressure versus high vacuum deposition. <i>Surface Science</i> , <b>2007</b> , 601, 4395-4401	1.8	53
151	Shape modification of III-V nanowires: the role of nucleation on sidewalls. <i>Physical Review E</i> , <b>2008</b> , 77, 031606	2.4	52
150	N-Polar GaN Nanowires Seeded by Al Droplets on Si(111). <i>Crystal Growth and Design</i> , <b>2012</b> , 12, 2724-2729	3.5	51
149	Second-harmonic generation in a doubly resonant semiconductor microcavity. <i>Optics Letters</i> , <b>1997</b> , 22, 1775-7	3	51

148	Phase Selection in Self-catalyzed GaAs Nanowires. <i>Nano Letters</i> , <b>2020</b> , 20, 1669-1675	11.5	49
147	Morphology and composition of highly strained InGaAs and InGaAsN layers grown on GaAs substrate. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 203-205	3.4	49
146	Effect of temperature on the optical properties of GaAsSbN/GaAs single quantum wells grown by molecular-beam epitaxy. <i>Journal of Applied Physics</i> , <b>2003</b> , 93, 4475-4479	2.5	48
145	Zinc blende GaAsSb nanowires grown by molecular beam epitaxy. <i>Nanotechnology</i> , <b>2008</b> , 19, 275605	3.4	46
144	Role of nitrogen in the mobility drop of electrons in modulation-doped GaAsN/AlGaAs heterostructures. <i>Solid State Communications</i> , <b>2003</b> , 126, 333-337	1.6	46
143	The role of surface diffusion of adatoms in the formation of nanowire crystals. <i>Semiconductors</i> , <b>2006</b> , 40, 1075-1082	0.7	45
142	Investigations on GaInNAsSb quinary alloy for 1.5 $\mu$ m laser emission on GaAs. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1298-1300	3.4	45
141	Observation of Bloch conduction perpendicular to interfaces in a superlattice bipolar transistor. <i>Applied Physics Letters</i> , <b>1986</b> , 49, 1260-1262	3.4	45
140	Photoreflectance, photoluminescence, and microphotoluminescence study of optical transitions between delocalized and localized states in GaN <sub>0.02</sub> As <sub>0.98</sub> , Ga <sub>0.95</sub> In <sub>0.05</sub> N <sub>0.02</sub> As <sub>0.98</sub> , and GaN <sub>0.02</sub> As <sub>0.90</sub> Sb <sub>0.08</sub> layers. <i>Physical Review B</i> , <b>2013</b> , 88,	3.3	44
139	Photoreflectance investigations of the energy level structure in GaInNAs-based quantum wells. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, S3071-S3094	1.8	43
138	Abrupt GaP/GaAs Interfaces in Self-Catalyzed Nanowires. <i>Nano Letters</i> , <b>2015</b> , 15, 6036-41	11.5	42
137	Sharpening the Interfaces of Axial Heterostructures in Self-Catalyzed AlGaAs Nanowires: Experiment and Theory. <i>Nano Letters</i> , <b>2016</b> , 16, 1917-24	11.5	41
136	Piezo-generator integrating a vertical array of GaN nanowires. <i>Nanotechnology</i> , <b>2016</b> , 27, 325403	3.4	41
135	Influence of shadow effect on the growth and shape of InAs nanowires. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 104317	2.5	40
134	Spin dynamics in dilute nitride semiconductors at room temperature. <i>Applied Physics Letters</i> , <b>2005</b> , 87, 252115	3.4	40
133	Thermal optimization of 1.55 $\mu$ m OP-VECSEL with hybrid metal/metamorphic mirror for single-mode high power operation. <i>Optical and Quantum Electronics</i> , <b>2008</b> , 40, 155-165	2.4	36
132	Measuring and Modeling the Growth Dynamics of Self-Catalyzed GaP Nanowire Arrays. <i>Nano Letters</i> , <b>2018</b> , 18, 701-708	11.5	35
131	Photoreflectance investigations of oscillator strength and broadening of optical transitions for GaAsSbGaInAs/GaAs bilayer quantum wells. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 3453-3455	3.4	35

130	Influence of carrier localization on modulation mechanism in photoreflectance of GaAsN and GaInAsN. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 1379-1381	3.4	35
129	Lattice-Mismatched Growth and Transport Properties of InAlAs/InGaAs Heterostructures on GaAs Substrates. <i>Japanese Journal of Applied Physics</i> , <b>1989</b> , 28, L1101-L1103	1.4	35
128	Electroabsorption modulators for high-bit-rate optical communications: a comparison of strained InGaAs/InAlAs and InGaAsP/InGaAsP MQW. <i>Semiconductor Science and Technology</i> , <b>1995</b> , 10, 887-901	1.8	34
127	Effect of nitrogen and temperature on the electronic band structure of GaAs <sub>1-x</sub> N <sub>x</sub> alloys. <i>Applied Physics Letters</i> , <b>2002</b> , 80, 2075-2077	3.4	33
126	Calculation of the temperature profile in nanowhiskers growing on a hot substrate. <i>Physical Review B</i> , <b>2006</b> , 73,	3.3	32
125	Photoluminescence characteristics of GaAsSbN/GaAs epilayers lattice-matched to GaAs substrates. <i>Solid State Communications</i> , <b>2004</b> , 132, 707-711	1.6	32
124	Comparison of light- and heavy-ion-irradiated quantum-wells for use as ultrafast saturable absorbers. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 2722-2724	3.4	32
123	Wurtzite GaAs/AlGaAs core-shell nanowires grown by molecular beam epitaxy. <i>Nanotechnology</i> , <b>2009</b> , 20, 415701	3.4	31
122	Investigation of the electronic transport in GaN nanowires containing GaN/AlN quantum discs. <i>Nanotechnology</i> , <b>2010</b> , 21, 425206	3.4	30
121	Electrical and optical characteristics of n-type-doped distributed Bragg mirrors on InP. <i>IEEE Photonics Technology Letters</i> , <b>1998</b> , 10, 763-765	2.2	30
120	Optical polarization relaxation in In <sub>x</sub> Ga <sub>1-x</sub> As-based quantum wells: Evidence of the interface symmetry-reduction effect. <i>Physical Review B</i> , <b>1998</b> , 58, R10179-R10182	3.3	30
119	Growth of vertical GaAs nanowires on an amorphous substrate via a fiber-textured Si platform. <i>Nano Letters</i> , <b>2013</b> , 13, 2743-7	11.5	29
118	Experimental investigation of the CMN matrix element in the band anticrossing model for GaAsN and GaInAsN layers. <i>Solid State Communications</i> , <b>2004</b> , 129, 353-357	1.6	29
117	Investigation of recombination processes involving defect-related states in (Ga,In)(As,Sb,N) compounds. <i>EPJ Applied Physics</i> , <b>2004</b> , 27, 313-316	1.1	29
116	Photon Cascade from a Single Crystal Phase Nanowire Quantum Dot. <i>Nano Letters</i> , <b>2016</b> , 16, 1081-5	11.5	28
115	Self-induced growth of vertical GaN nanowires on silica. <i>Nanotechnology</i> , <b>2016</b> , 27, 135602	3.4	28
114	Conduction band structure in wurtzite GaAs nanowires: A resonant Raman scattering study. <i>Applied Physics Letters</i> , <b>2012</b> , 100, 073102	3.4	27
113	Effect of arsenic species on the kinetics of GaAs nanowires growth by molecular beam epitaxy. <i>Journal of Crystal Growth</i> , <b>2010</b> , 312, 2073-2077	1.6	27

112	Quantum-well saturable absorber at 1.55 $\mu\text{m}$ on GaAs substrate with a fast recombination rate. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 201110	3-4	27
111	Ultrafast saturable absorption at 1.55 $\mu\text{m}$ in heavy-ion-irradiated quantum-well vertical cavity. <i>Applied Physics Letters</i> , <b>2000</b> , 76, 1371-1373	3-4	27
110	Energy harvesting efficiency in GaN nanowire-based nanogenerators: the critical influence of the Schottky nanocontact. <i>Nanoscale</i> , <b>2017</b> , 9, 4610-4619	7-7	24
109	Determination of n-Type Doping Level in Single GaAs Nanowires by Cathodoluminescence. <i>Nano Letters</i> , <b>2017</b> , 17, 6667-6675	11.5	24
108	Effect of nitrogen in the electronic structure of GaAsN and GaAsSb(N) compounds. <i>Materials Science and Engineering C</i> , <b>2002</b> , 21, 251-254	8.3	23
107	Quasi one-dimensional transport in single GaAs/AlGaAs core-shell nanowires. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 142114	3-4	22
106	GaN nanowires for piezoelectric generators. <i>Physica Status Solidi - Rapid Research Letters</i> , <b>2014</b> , 8, 414-419	4-5	21
105	Subpicosecond pulse generation from a 1.56 $\mu\text{m}$ mode-locked VECSEL. <i>Optics Letters</i> , <b>2011</b> , 36, 4377-9	3	21
104	GaP/GaAs $_{1-x}$ P $_x$ nanowires fabricated with modulated fluxes: A step towards the realization of superlattices in a single nanowire. <i>Journal of Crystal Growth</i> , <b>2011</b> , 323, 293-296	1.6	21
103	Spin-dependent photoconductivity in nonmagnetic semiconductors at room temperature. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 241104	3-4	19
102	Growth and structural characterization of GaAs/GaAsSb axial heterostructured nanowires. <i>Journal of Crystal Growth</i> , <b>2009</b> , 311, 1847-1850	1.6	19
101	In situ passivation of GaAsP nanowires. <i>Nanotechnology</i> , <b>2017</b> , 28, 495707	3-4	18
100	Growth of Inclined GaAs Nanowires by Molecular Beam Epitaxy: Theory and Experiment. <i>Nanoscale Research Letters</i> , <b>2010</b> , 5, 1692-7	5	18
99	Class-A dual-frequency VECSEL at telecom wavelength. <i>Optics Letters</i> , <b>2014</b> , 39, 5586-9	3	17
98	InP $_{1-x}$ As $_x$ quantum dots in InP nanowires: A route for single photon emitters. <i>Journal of Crystal Growth</i> , <b>2013</b> , 378, 519-523	1.6	17
97	Band discontinuities in In $_x$ Ga $_{1-x}$ As-InP and InP-Al $_y$ In $_{1-y}$ As heterostructures: Evidence of noncommutativity. <i>Physical Review B</i> , <b>1997</b> , 55, 2274-2279	3-3	17
96	The effect of potential fluctuations on the optical properties of InGaAs $_{1-x}$ AlAs superlattices. <i>Journal of Applied Physics</i> , <b>2005</b> , 97, 103518	2.5	17
95	MBE growth of InAsN on (100) InAs substrates. <i>Physica Status Solidi (B): Basic Research</i> , <b>2005</b> , 242, R43-R45	4-5	16

94	Impact of the GaN nanowire polarity on energy harvesting. <i>Applied Physics Letters</i> , <b>2014</b> , 104, 213105	3.4	15
93	Effect of nitrogen on the GaAs <sub>0.9</sub> N <sub>x</sub> Sb <sub>0.1</sub> dielectric function from the near-infrared to the ultraviolet. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 201903	3.4	15
92	Giant spin-dependent photo-conductivity in GaAsN dilute nitride semiconductor. <i>Physical Review B</i> , <b>2011</b> , 83,	3.3	15
91	Electroabsorption modulator based on Wannier-Stark localization with 20 GHz/V efficiency. <i>Applied Physics Letters</i> , <b>1992</b> , 61, 2773-2775	3.4	15
90	Room-temperature optical manipulation of nuclear spin polarization in GaAsN. <i>Physical Review B</i> , <b>2014</b> , 90,	3.3	14
89	Floor free 10-Gb/s transmission with directly modulated GaInNAs-GaAs 1.35- $\mu$ m laser for metropolitan applications. <i>IEEE Photonics Technology Letters</i> , <b>2005</b> , 17, 971-973	2.2	14
88	Fabrication of an InGaAs spin filter by implantation of paramagnetic centers. <i>Applied Physics Letters</i> , <b>2013</b> , 103, 052403	3.4	13
87	Random stacking sequences in III-V nanowires are correlated. <i>Physical Review B</i> , <b>2014</b> , 89,	3.3	13
86	Electron spin control in dilute nitride semiconductors. <i>Journal of Physics Condensed Matter</i> , <b>2009</b> , 21, 174211	1.8	13
85	Scaling of the saturation energy in microcavity saturable absorber devices. <i>Applied Physics Letters</i> , <b>2006</b> , 88, 153513	3.4	13
84	Ultrafast InGaAs/InGaAlAs multiple-quantum-well electro-absorption modulator for wavelength conversion at high bit rates. <i>Applied Physics Letters</i> , <b>2004</b> , 84, 4268-4270	3.4	13
83	. <i>IEEE Journal of Quantum Electronics</i> , <b>2012</b> , 48, 643-650	2	12
82	Band structure calculations for dilute nitride quantum wells under compressive or tensile strain. <i>Journal of Physics Condensed Matter</i> , <b>2004</b> , 16, S3215-S3227	1.8	12
81	Photoluminescence of an InAlAs/InGaAs Quantum Well Structure Grown on a GaAs Substrate. <i>Japanese Journal of Applied Physics</i> , <b>1990</b> , 29, L233-L235	1.4	12
80	Morphology Tailoring and Growth Mechanism of Indium-Rich InGaN/GaN Axial Nanowire Heterostructures by Plasma-Assisted Molecular Beam Epitaxy. <i>Crystal Growth and Design</i> , <b>2018</b> , 18, 2545-2554	3.5	11
79	Optical polarization properties of InAs/InP quantum dot and quantum rod nanowires. <i>Nanotechnology</i> , <b>2015</b> , 26, 395701	3.4	11
78	Effect of diffusion from a lateral surface on the rate of GaN nanowire growth. <i>Semiconductors</i> , <b>2012</b> , 46, 838-841	0.7	11
77	Growth, structure and phase transitions of epitaxial nanowires of III-V semiconductors. <i>Journal of Physics: Conference Series</i> , <b>2010</b> , 209, 012002	0.3	11

76	Ultrashort pulse generation from 1.56 $\mu\text{m}$ mode-locked VECSEL at room temperature. <i>Optics Express</i> , <b>2010</b> , 18, 19902-13	3.3	11
75	Si Incorporation in InP Nanowires Grown by Au-Assisted Molecular Beam Epitaxy. <i>Journal of Nanomaterials</i> , <b>2009</b> , 2009, 1-7	3.2	11
74	Selective Area Growth of GaN Nanowires on Graphene Nanodots. <i>Crystal Growth and Design</i> , <b>2020</b> , 20, 552-559	3.5	11
73	Modeling, synthesis and study of highly efficient solar cells based on III-nitride nanowire arrays grown on Si substrates. <i>Journal of Physics: Conference Series</i> , <b>2015</b> , 643, 012115	0.3	10
72	Low power all-optical bistability in InGaAs-AlInAs superlattices: Demonstration of a wireless self-electro-optical effect device operating at 1.5 $\mu\text{m}$ . <i>Applied Physics Letters</i> , <b>1994</b> , 64, 742-744	3.4	10
71	Investigation of low-power all-optical bistability in an InGaAs-InAs superlattice. <i>Semiconductor Science and Technology</i> , <b>1995</b> , 10, 881-885	1.8	9
70	Nanoscale electrical analyses of axial-junction GaAsP nanowires for solar cell applications. <i>Nanotechnology</i> , <b>2020</b> , 31, 145708	3.4	9
69	Electron beam induced current microscopy investigation of GaN nanowire arrays grown on Si substrates. <i>Materials Science in Semiconductor Processing</i> , <b>2016</b> , 55, 72-78	4.3	8
68	Femtosecond pulse generation around 1500 nm using a GaInNAsSb SESAM. <i>Optics Express</i> , <b>2008</b> , 16, 18739-44	3.3	8
67	Competition between confinement potential fluctuations and band-gap renormalization effects in In <sub>0.53</sub> Ga <sub>0.47</sub> As/In <sub>0.525</sub> Ga <sub>0.235</sub> Al <sub>0.25</sub> As single and double quantum wells. <i>Physical Review B</i> , <b>2008</b> , 77,	3.3	8
66	InyGa <sub>1-x</sub> As/InyAl <sub>1-x</sub> As resonant tunneling diodes on GaAs. <i>Applied Physics Letters</i> , <b>1991</b> , 59, 111-113	3.4	8
65	Secondary ion mass spectrometry quantification of Be in Al <sub>x</sub> Ga <sub>1-x</sub> As/GaAs multilayer structures. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , <b>1988</b> , 6, 2243-2247	2.9	8
64	Shiba Bound States across the Mobility Edge in Doped InAs Nanowires. <i>Physical Review Letters</i> , <b>2017</b> , 119, 097701	7.4	7
63	The effect of potential fluctuations on the optical properties of InGaAs/InGaAlAs single and coupled double quantum wells. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 053519	2.5	7
62	Optimization and Characterization of InGaAsN/GaAs Quantum-well Ridge Laser Diodes for High Frequency Operation. <i>Optical and Quantum Electronics</i> , <b>2006</b> , 38, 313-324	2.4	7
61	Phase coherent transport in GaAs/AlGaAs core-shell nanowires. <i>Journal of Crystal Growth</i> , <b>2013</b> , 378, 546-548	1.6	6
60	Epitaxial growth and picosecond carrier dynamics of GaInAs/GaInNAs superlattices. <i>Applied Physics Letters</i> , <b>2009</b> , 95, 141910	3.4	6
59	Photoluminescence study of nitrogen effects on confined states in GaAs <sub>1-x</sub> N <sub>x</sub> GaAs quantum wells. <i>EPJ Applied Physics</i> , <b>2009</b> , 47, 30302	1.1	6



58	Clustering in GaAsSbN alloys as a possible origin of their atypical optical behavior: a Sb K-edge X-ray absorption study. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2006</b> , 3, 1931-1934		6
57	Photoluminescence study of interfaces between heavily doped Al <sub>0.48</sub> In <sub>0.52</sub> As:Si layers and InP (Fe) substrates. <i>Journal of Applied Physics</i> , <b>2002</b> , 91, 8999-9004	2.5	6
56	Investigation of optical properties of interfaces between heavily doped Al <sub>0.48</sub> In <sub>0.52</sub> As:Si and InP (Fe) substrates by photoreflectance analysis. <i>Journal of Applied Physics</i> , <b>1999</b> , 85, 4184-4188	2.5	6
55	Highly thermally stable electrical compensation in oxygen implanted p-InAlAs. <i>Applied Physics Letters</i> , <b>1993</b> , 62, 867-869	3.4	6
54	Shubnikov-de Haas - like oscillations in the vertical transport of semiconductor superlattices. <i>Brazilian Journal of Physics</i> , <b>1999</b> , 29, 375-379	1.2	6
53	GaN/Ga <sub>2</sub> O <sub>3</sub> Core/Shell Nanowires Growth: Towards High Response Gas Sensors. <i>Applied Sciences (Switzerland)</i> , <b>2019</b> , 9, 3528	2.6	5
52	Class-A operation of an optically-pumped 1.6 μm-emitting quantum dash-based vertical-external-cavity surface-emitting laser on InP. <i>Optics Express</i> , <b>2017</b> , 25, 11760-11766	3.3	5
51	Effects of repulsive and attractive ionized impurities on the resistivity of semiconductor heterostructures in the quantum Hall regime. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	5
50	Semiconductor quantum-wires and nano-wires for optoelectronic applications. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2009</b> , 20, 94-101	2.1	5
49	Magnetic thaw down and boil-off of electrons in the quantum Hall effect regime due to magnetoacceptors in GaAs/GaAlAs heterostructures. <i>Physical Review B</i> , <b>2012</b> , 86,	3.3	5
48	Effect of deposition conditions on nanowhisker morphology. <i>Semiconductors</i> , <b>2007</b> , 41, 865-874	0.7	5
47	Photoluminescence properties of a Si doped InGaAs/InGaAlAs superlattice. <i>Journal of Physics Condensed Matter</i> , <b>2007</b> , 19, 086207	1.8	5
46	InGaAs/InAlAs(Si) modulation-doped heterostructures intentionally lattice mismatched to InP substrates. <i>Journal of Applied Physics</i> , <b>1989</b> , 66, 2633-2636	2.5	5
45	Investigation of GaN nanowires containing AlN/GaN multiple quantum discs by EBIC and CL techniques. <i>Nanotechnology</i> , <b>2019</b> , 30, 214006	3.4	4
44	Picosecond carrier lifetimes in dilute GaInNAs grown on InP substrate. <i>Applied Physics Letters</i> , <b>2011</b> , 99, 141902	3.4	4
43	Potential of semiconductor nanowires for single photon sources <b>2009</b> ,		4
42	Potential-inserted InGaAs - AlGaInAs shallow quantum wells for electro-optical modulation at. <i>Semiconductor Science and Technology</i> , <b>1997</b> , 12, 729-732	1.8	4
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37	Stable and high yield growth of GaP and InGaAs nanowire arrays using In as a catalyst. <i>Nanoscale</i> , <b>2020</b> , 12, 18240-18248	7-7	4
36	Crystallization of Si Templates of Controlled Shape, Size, and Orientation: Toward Micro- and Nanosubstrates. <i>Crystal Growth and Design</i> , <b>2015</b> , 15, 2102-2109	3-5	3
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34	Palladium assisted heteroepitaxial growth of an InAs nanowire by molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , <b>2014</b> , 29, 115005	1.8	3
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29	Growth Dynamics of Gallium Nanodroplets Driven by Thermally Activated Surface Diffusion. <i>Journal of Physical Chemistry Letters</i> , <b>2019</b> , 10, 5082-5089	6.4	2
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15	Nitride Nanowires: From Rigid to Flexible Piezo-generators. <i>Journal of Physics: Conference Series</i> , <b>2016</b> , 773, 012010	0.3	1
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